Switch-mode Schottky Power Rectifier

Surface Mount Power Package

MBRD5H100, NBRD5H100

This series of Power Rectifiers employs the Schottky Barrier principle in a large metal to silicon power diode. State of the art geometry features epitaxial construction with oxide passivation and metal overlay contact. Ideally suited for use in low voltage, high frequency switching power supplies, free wheeling diodes, and polarity protection diodes.

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SCHOTTKY BARRIER RECTIFIER 5 AMPERES, 100 VOLTS

Features

- Guardring for Stress Protection
- Low Forward Voltage
- 175°C Operating Junction Temperature
- Epoxy Meets UL 94 V 0 @ 0.125 in
- Short Heat Sink Tab Manufactured Not Sheared!
- NBRD Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC Q101 Qualified and PPAP Capable
- These Devices are Pb Free and are RoHS Compliant*

Mechanical Characteristics:

- Case: Epoxy, Molded, Epoxy Meets UL 94 V 0
- Weight: 0.4 grams (approximately)
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead and Mounting Surface Temperature for Soldering Purposes: 260°C Max. for 10 Seconds
- Device Meets MSL1 Requirements
- ESD Ratings:
  - Machine Model = C (> 400 V)
  - Human Body Model = 3B (> 8000 V)

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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Publication Order Number:
MBRD5H100/D

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	100	V
Average Rectified Forward Current T_C = 171°C	$I_{F(AV)}$	5	A
Peak Repetitive Forward Current (Square Wave, Duty = 0.5) T_C = 171°C	I_{FRM}	10	A
Nonrepetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60 Hz)	I_{FSM}	105	A
Operating Junction and Storage Temperature Range (Note 1)	T_J, T_{stg}	−65 to +175	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. The heat generated must be less than the thermal conductivity from Junction−to−Ambient: $dP_D/dT_J < 1/R_{\theta JA}$.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Value	Unit
Thermal Resistance Junction−to−Case (Note 2) Junction−to−Ambient (Note 2)	 $R_{\theta JC}$ $R_{\theta JA}$	 1.6 95.8	°C/W

2. When mounted using minimum recommended pad size on FR−4 board.

ELECTRICAL CHARACTERISTICS

Characteristic	Symbol	Value	Unit
Maximum Instantaneous Forward Voltage (Note 3) (I_F = 5 A, T_J = 25°C) (I_F = 5 A, T_J = 125°C)	V_F	 0.71 0.60	V
Maximum Instantaneous Reverse Current (Note 3) (Rated dc Voltage, T_J = 125°C) (Rated dc Voltage, T_J = 25°C)	I_R	 4.5 3.5	 mA μA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. Pulse Test: Pulse Width = 300 μs, Duty Cycle ≤ 2.0%

TYPICAL CHARACTERISTICS

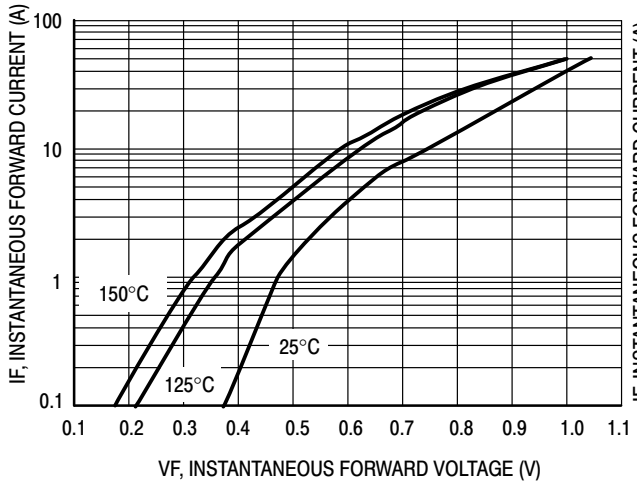


Figure 1. Typical Forward Voltage

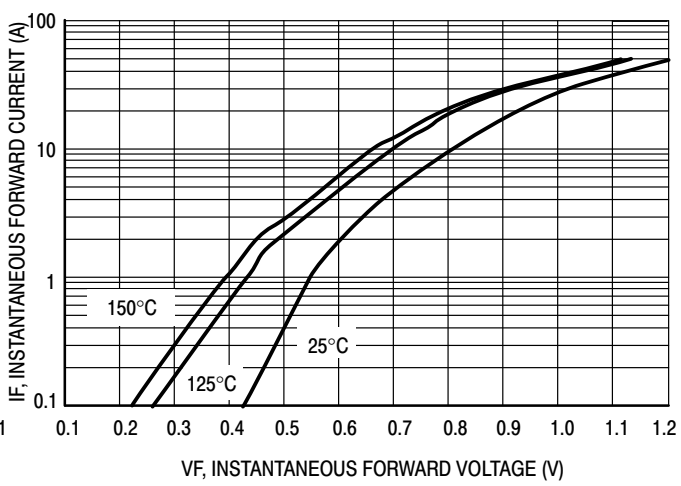
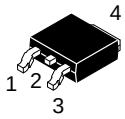


Figure 2. Maximum Forward Voltage



SCALE 1:1

DPAK (SINGLE GAUGE)
CASE 369C
ISSUE G

DATE 31 MAY 2023

STYLE 1:
PIN 1. BASE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

STYLE 2:
PIN 1. GATE
2. DRAIN
3. SOURCE
4. DRAIN

STYLE 3:
PIN 1. ANODE
2. CATHODE
3. ANODE
4. CATHODE

STYLE 4:
PIN 1. CATHODE
2. ANODE
3. GATE
4. ANODE

STYLE 5:
PIN 1. GATE
2. ANODE
3. CATHODE
4. ANODE

STYLE 6:
PIN 1. MT1
2. MT2
3. GATE
4. MT2

STYLE 7:
PIN 1. GATE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

STYLE 8:
PIN 1. N/C
2. CATHODE
3. ANODE
4. CATHODE

STYLE 9:
PIN 1. ANODE
2. CATHODE
3. RESISTOR ADJUST
4. CATHODE

STYLE 10:
PIN 1. CATHODE
2. ANODE
3. CATHODE
4. ANODE